

Kazuma Eto

List of Publications by Year in descending order

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14
papers

1,049
citations

1040056

9
h-index

1058476

14
g-index

14
all docs

14
docs citations

14
times ranked

1903
citing authors

#	ARTICLE	IF	CITATIONS
1	Spin-Electricity Conversion Induced by Spin Injection into Topological Insulators. Physical Review Letters, 2014, 113, 196601.	7.8	290
2	Unexpected mass acquisition of Dirac fermions at the quantum phase transition of a topological insulator. Nature Physics, 2011, 7, 840-844.	16.7	215
3	Angular-dependent oscillations of the magnetoresistance in Bi_2Te_3 to the three-dimensional bulk Fermi surface. Physical Review B, 2010, 81, .	3.2	182
4	Manipulation of Topological States and the Bulk Band Gap Using Natural Heterostructures of a Topological Insulator. Physical Review Letters, 2012, 109, 236804.	7.8	84
5	Topological Surface States in Lead-Based Ternary Telluride $\text{Pb}_2\text{Bi}_2\text{Te}_5$. Physical Review Letters, 2012, 108, 116801.	7.8	64
6	Relationship between Fermi surface warping and out-of-plane spin polarization in topological insulators: A view from spin- and angle-resolved photoemission. Physical Review B, 2014, 89, .	3.2	54
7	Robust Protection from Backscattering in the Topological Insulator Bi_2Te_3 . Physical Review Letters, 2014, 112, 076801.	7.8	53
8	Spin Polarization of Gapped Dirac Surface States Near the Topological Phase Transition in $\text{TI}_2\text{Bi}_2\text{Te}_5$. Physical Review Letters, 2014, 112, 076802.	7.8	42
9	¹⁸⁶ Growth of P-type 4H-SiC single crystals by physical vapor transport using aluminum and nitrogen co-doping. Journal of Crystal Growth, 2017, 470, 154-158.	1.5	20
10	Hopping conduction range of heavily Al-doped 4H-SiC thick epilayers grown by CVD. Applied Physics Express, 2015, 8, 121302.	2.4	12
11	Evaluation of the increase in threading dislocation during the initial stage of physical vapor transport growth of 4H-SiC. Japanese Journal of Applied Physics, 2018, 57, 065501.	1.5	10
12	Difference of double Shockley-type stacking faults expansion in highly nitrogen-doped and nitrogen-boron co-doped n-type 4H-SiC crystals. Journal of Crystal Growth, 2017, 468, 879-882.	1.5	9
13	Growth of Low Resistivity n-Type 4H-SiC Bulk Crystals by Sublimation Method Using Co-Doping Technique. Materials Science Forum, 2014, 778-780, 47-50.	0.3	8
14	Spin-orbit coupling and anomalous angular-dependent magnetoresistance in the quantum transport regime of PbS. Physical Review B, 2010, 81, .	3.2	6